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orientation. Current flow of device is along <100> direction.
The mobility of PMOS could be enhanced on this direction.

0012 These and other embodiments, aspects and features of the invention will be better understood from a detailed description of the preferred embodiments of the invention which are further described below in conjunction with the accompanying Figures.

BRIEF DESCRIPTION OF THE DRAWINGS

0013 Figures 1A-1F are cross sectional views including a portion of a gate structure of an exemplary MOSFET showing exemplary manufacturing stages in an integrated circuit manufacturing process according to an embodiment of the present invention.

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0014 Figures 2A-2^E~~D~~ are cross sectional views including a portion of a gate structure of an exemplary MOSFET showing exemplary manufacturing stages in an integrated circuit manufacturing process according to an embodiment of the present invention.

0015 Figure 3 is a data representation showing the gain in channel stress achieved according to the Slim spacer MOSFET device formed according to embodiments of the present invention.